# SPICE Device Model SiHG17N60D



**Vishay Siliconix** 

## **D** Series Power MOSFET

### DESCRIPTION

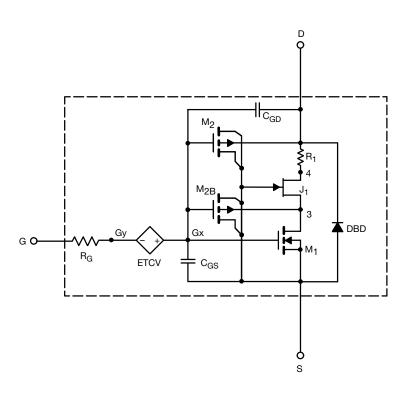
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the -55 °C to 125 °C temperature ranges under the pulsed 0 V to 15 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{\rm gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### **CHARACTERISTICS**

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- · Apply for both Linear and Switching Application
- Accurate over the -55 °C to +125 °C Temperature Range
- Model the Gate Charge

## SUBCIRCUIT MODEL SCHEMATIC



#### Note

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



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| <b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted) |                     |  |                   |                  |      |
|--|---------------------|--|-------------------|------------------|------|
| PARAMETER  | SYMBOL              | TEST CONDITIONS  | SIMULATED<br>DATA | MEASURED<br>DATA | UNIT |
| Static   |                     |  |                   |                  |      |
| Gate Threshold Voltage   | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$  | 3.5               | -                | V    |
| Drain-Source On-State Resistance <sup>a</sup>                          | R <sub>DS(on)</sub> | $V_{GS} = 10 \text{ V}, \text{ I}_{D} = 8 \text{ A}$                                 | 0.305             | 0.275            | Ω    |
| Forward Transconductance <sup>a</sup>                                  | g <sub>fs</sub>     | $V_{DS} = 50 \text{ V}, \text{ I}_{D} = 8 \text{ A}$                                 | 7                 | 6.2              | S    |
| Body Diode Voltage   | V <sub>SD</sub>     | $I_{\rm S} = 8$ A, $V_{\rm GS} = 0$ V  | 0.83              | -                | V    |
| Dynamic <sup>b</sup>   |                     |  |                   |                  |      |
| Input Capacitance  | C <sub>iss</sub>    | $V_{DS}$ = 100 V, $V_{GS}$ = 0 V, f = 1 MHz  | 1830              | 1780             | pF   |
| Output Capacitance   | C <sub>oss</sub>    |  | 139               | 140              |      |
| Reverse Transfer Capacitance   | C <sub>rss</sub>    |  | 15                | 15               |      |
| Total Gate Charge  | Qg                  | $V_{DS} = 480 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 8 \text{ A}$ | 45                | 45               | nC   |
| Gate-Source Charge   | Q <sub>gs</sub>     |  | 14                | 14               |      |
| Gate-Drain Charge  | Q <sub>gd</sub>     |  | 22                | 22               |      |

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$ 

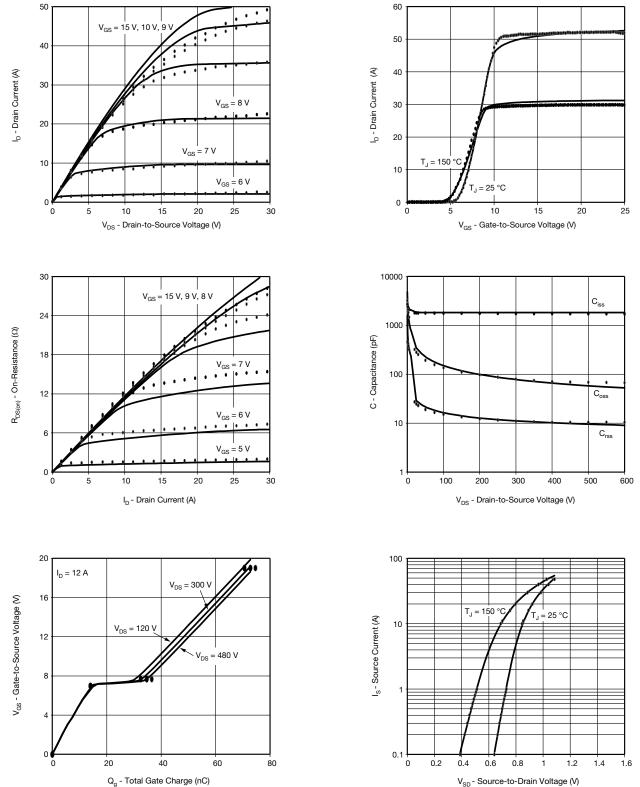
b. Guaranteed by design, not subject to production testing.

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## COMPARISON OF MODEL WITH MEASURED DATA (T<sub>J</sub> = 25 °C, unless otherwise noted)



#### Note

• Dots and squares represent measured data. Copyright: Vishay Intertechnology, Inc.

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